

光鋐科技股份有限公司

Epileds Technologies, Inc.

Product specification of 13 x10 mil blue LED chip

1. Scope:

This specification applies to InGaN/GaN 13 x 10mil blue LED chip, EP-B1310A-A1 ◦

2. Materials :

2.1 P-contact : Conductive Layer ◦

2.2 P-pad : Au ◦

2.3 N-pad : Au ◦

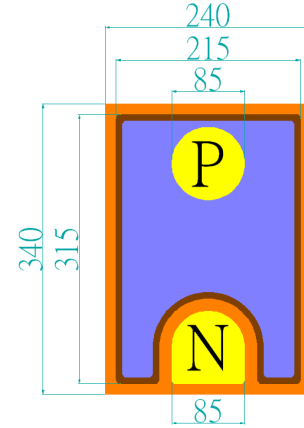
3. Dimensions :

3.1 Chip size : 340μm x 240μm ◦

3.2 P-pad : φ85μm, thickness 1.2μm ◦

3.3 N-pad : φ85μm, thickness 1.2μm ◦

3.4 Chip thickness : 90μm±10μm ◦



4. Electro-optical characteristics and specification: (Tc=25°C)

4.1 Electro-optical characteristics

Test parameter	Condition	Min	Typ	Max	Unit
Dominant wavelength(Wd)	20mA	445	-	475	nm
Radiant intensity(I)	20mA	4.1	-	10.3	mW/sr
Forward voltage(Vf4)	1uA	1.9	-	2.5	V
Forward voltage(Vf1)	20mA	2.8	-	3.8	V
Reverse current (Ir)	-8V	0	-	0.5	uA
Electrostatic discharge characteristic (ESD)	HBM	1000	-	-	V

4.2 Electro-optical specification(Bin table) :

Wd		I		Vf1 (V)	Vf4 (V)	Ir (uA)
Bin	nm	Bin	mW/sr			
PS	445~447.5	19	4.1~4.4	2.8~3.8	1.9~2.5	0~0.5
PT	447.5~450	20	4.4~4.8			
BA	450~452.5	21	4.8~5.2			
BB	452.5~455	22	5.2~5.6			
BC	455~457.5	23	5.6~6.0			
BD	457.5~460	24	6.0~6.5			
BE	460~462.5	25	6.5~7.0			
BF	462.5~465	26	7.0~7.6			
BG	465~467.5	27	7.6~8.2			
BH	467.5~470	28	8.2~8.8			
BI	470~472.5	29	8.8~9.5			
BJ	472.5~475	30	9.5~10.3			

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* The detail technical and reliability datasheet are also available for your reference, please be free to contact us.